AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): Tsukasa Yajima								Docket No. PNET.009D	
l .	Serial No. 09/768,271 J		Filing Date January 25, 2001		Examiner A. Mai			Group Art Unit 2814	
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Typed or Printed Name of Person Mailing Correspondence



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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE -4 2002

In re PATENT APPLICATION of

Group Art Unit: 2814

13/01-7-02

Tsukasa Yajima

Examiner: A. Mai

A. Welly

Serial No.: 09/768,271

Filed: January 25, 2001

For: SEMICONDUCTOR DEVICE HAVING PROTECTIVE LAYER ON FIELD OXIDE

## **AMENDMENT**

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

Date: October 31, 2002

Sir:

In response to the Office Action dated July 31, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

## In the Specification:

Replace the paragraph beginning on page 13, line 12 with the following paragraph:

"Thereafter, the side-wall 37 is formed by implementing the anisotropic etching such as the RIE with respect to the oxide layer 36 (FIG. 1(h)). Then, the insulating layer 50 and the contact holes 52 are formed, and the aluminum wiring 54 is conducted by the normal processes, thus completing the MOSFET (FIG. 1(i))."

In the Claims: